

**● PRINTER RUSH ●**  
**(PTO ASSISTANCE)**

4th Request

Application :	Examiner :	GAU :
09/945512	Booth	2812
From: T.N.C.Bill	Location: <input checked="" type="radio"/> IDC FMF FDC	Date: 11/3/04
Tracking #: 5974753		Week Date: 75-04

DOC CODE	DOC DATE	MISCELLANEOUS
<input checked="" type="checkbox"/> 449	9-22-03	<input type="checkbox"/> Continuing Data
<input checked="" type="checkbox"/> IDS		<input type="checkbox"/> Foreign Priority
<input type="checkbox"/> CLM		<input type="checkbox"/> Document Legibility
<input type="checkbox"/> IIFW		<input type="checkbox"/> Fees
<input type="checkbox"/> SRFW		<input type="checkbox"/> Other
<input type="checkbox"/> DRW		
<input type="checkbox"/> OATH		
<input type="checkbox"/> 312		
<input type="checkbox"/> SPEC		

<p>[RUSH] MESSAGE: <u>Attn: Lori Burch, supervisor Query Branch</u></p> <p><u>PTO-1449: Please either initial or line through citation. Copy provided for reference.</u></p> <p style="text-align: right;"><u>thank you</u></p>
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<p>[XRUSH] RESPONSE:</p> <hr/> <hr/> <hr/> <hr/> <hr/>
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INITIALS:

NOTE: This form will be included as part of the official USPTO record, with the Response document coded as XRUSH.

REV 10/04

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		Complete if Known				
		Application Number	09/945512			
		Filing Date	August 30, 2001			
		First Named Inventor	Forbes, Leonard			
		Group Art Unit	2812			
		Examiner Name	Booth, Richard			
Sheet 1 of 1		Attorney Docket No: 1303.027US1				

**O I P E**  
SEP 22 2003  
U.S. PATENT & TRADEMARK OFFICE

**US PATENT DOCUMENTS**

Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-5,952,692	09/14/1999	Nakazato, K. , et al.	257	321	10/28/1997
	US-6,210,999	04/03/2001	Gardner, , et al.	438	183	12/04/1998
	US-6,475,857	11/05/2002	Kim, W. , et al.	438	240	06/21/2001
	US-6,541,280	04/01/2003	Kaushik, , et al.			03/20/2001

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		SHI, Y. , "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", IEEE Electron Device Letters, 19(10), (1998),pp. 388-390	
		ZHANG, "Atomic Layer Deposition of High Dielectric Constant Nanolaminates", Journal of The Electrochemical Society, 148(4),(2001),F63-F66	

**EXAMINER****DATE CONSIDERED**